Q. P. Code: 24887

Max. Marks:80



**Duration:** 3hrs

5

5

NB:

- (1) Question No.1 is compulsory.
- (2) Answer any **three** from remaining questions.
- (3) Figures to the right indicate full marks.
- (4) Assume suitable data if required.

## Q.1 Attempt any four

- Give the equation for the current in semiconductor diode. With the help of this equation explain in detail the V-I characteristics of a semiconductor diode.
- b Explain effect of temperature on JFET and derive equation for zero temperature drift.
- For the circuit shown in fig 1 determine small signal hybrid pi parameters of transistor.

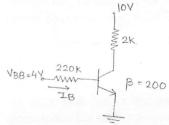


Fig.1

d Design clipper circuit for the output shown in figure.2 Assume diode is ideal.

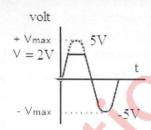


Fig.2

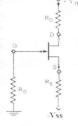


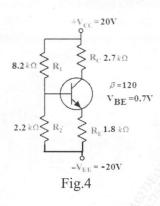
Fig.3

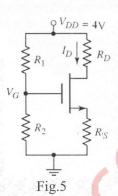
For the FET shown in figure.3 the drain current equation is  $I_{DQ} = 9\left(1 + \frac{V_{GSQ}}{3}\right)^2$  mA. Determine  $I_{DQ}$ ,  $V_{GSQ}$ ,  $V_{DSQ}$ ,  $V_{DD} = 18V$ ,  $R_D = 2.2k\Omega$ ,  $R_S = 1.2k\Omega$ ,  $-V_{SS} = -9V$  and  $R_G = 1M\Omega$ .

Q.2

a For the circuit shown in Fig.4 determine the  $V_{ECQ}$ ,  $I_{CQ}$ ,  $V_C$ , and  $V_E$ .

10





b Design the circuit shown in Fig.5 such that  $V_{GS}$ =0.50V and  $V_{DS}$ =2.5V. The transistor parameters are:  $V_{TN}$ =0.24V, Kn=1.1mA/V2, and  $\lambda$ =0. Let  $R_1$ + $R_2$ =50K $\Omega$ .

Q.3

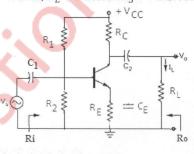
- a Analyze and derive the expression for the voltage gain, input impedance and output impedance for common collector amplifier with voltage divider biasing.
- b For the amplifier shown in Fig.6 analyze and determine.

10

- i. Small-signal voltage gain.
- ii. Input and output impedance.

BJT and circuit parameters are:  $\beta = 100, V_{BE} = 0.7V$ .  $R_1 = 56k\Omega$ ,  $R_2 = 12.2k\Omega$ ,

$$R_E = 0.4k\,\Omega,\; R_C = 2k\,\Omega, R_L = 10k\,\Omega\,R_S = 0.5k\,\Omega, V_{CC} = 10V$$



Q.4

- a Draw the structure of an N-channel Enhancement type MOSFET. Explain its working 10 with the help of output drain characteristics and transfer characteristics.
- b For the MOSFET common source amplifier shown in fig.7 determine output voltage, input impedance and output impedance. Given:  $V_{TN} = 1V$ ,  $K_N = 0.5 \text{ mA/V}^2$ ,  $\lambda = 0.01 \text{ V}^{-1}$ .

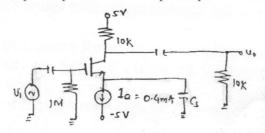


Fig.7

Q.5

- a Draw and explain energy band diagram of MOS capacitor in accumulation, depletion 10 and inversion region.
- b Derive the expression for frequency of oscillation for a transistorized (BJT) RC phase 10 shift oscillator.
- Q.6 Write a short note on following.
  - a Cristal oscillator and its application.
  - b Schottkey Diode (Construction and operation and application) 5
  - c Graphical analysis of BJT amplifier to determine parameters.
  - d h-Parameter equivalent circuit for BJT

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